

High Resolution Black Resist SEBK-401

Product	Vis. (cps)	S.C. (%)	OD (μm^{-1})	BT (sec)	Dev. Time (sec)	Adhesion (μm)	THK after PB (at 550rpm) (μm)	OD
401	3.5	20.5	4.0	40	60	3	1.0	4.0

Characteristic

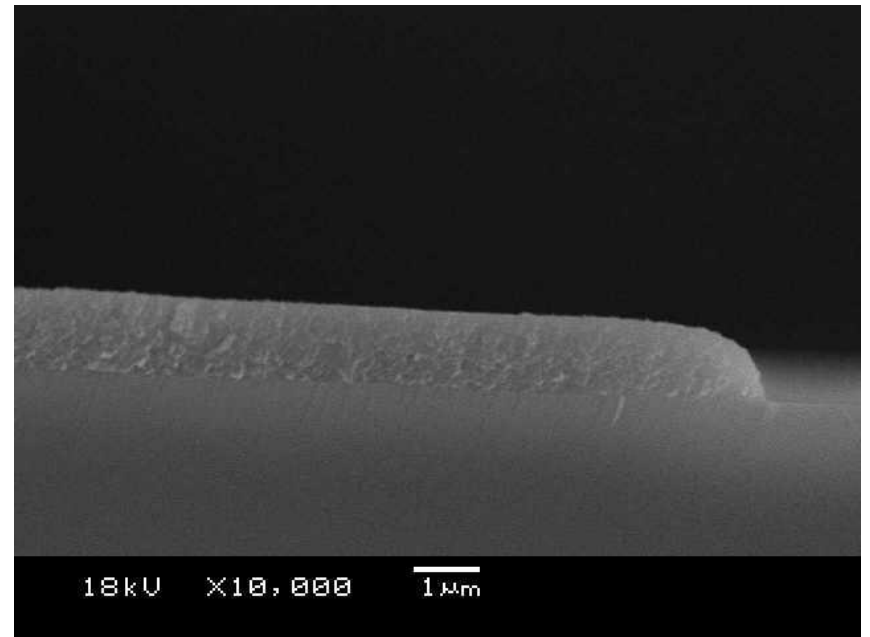
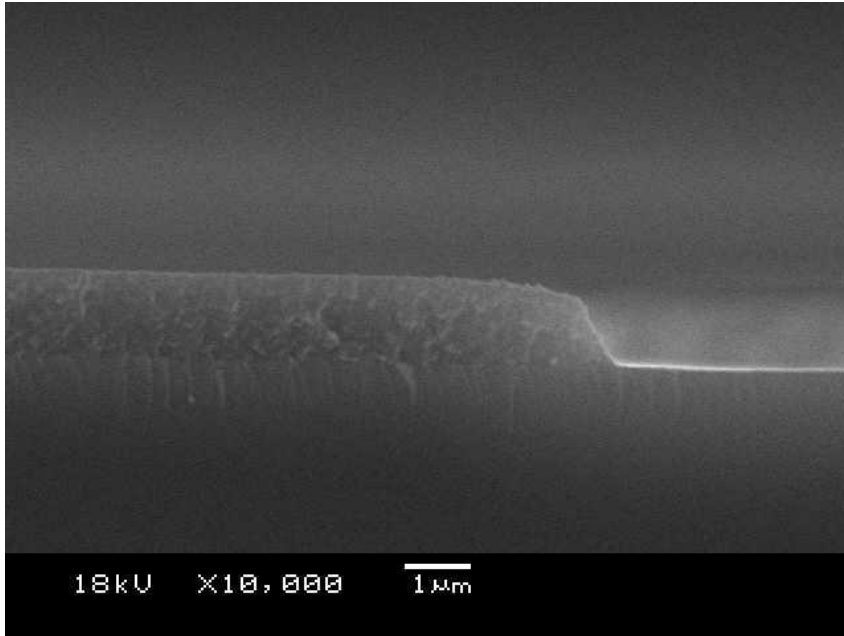
1. High Resolution (3 μm line & 1.5 μm hole)
2. High Optical Density (OD=4.0/ μm)
3. Low Tape-Angle(<90°)
4. Good Leveling
5. Low Transmittance at 1100nm

Applications

1. Black Matrix for TFT-LCD CF
2. Black Matrix for Micro LED
3. Micro Grating

<u>Process Parameter</u>	
Spin Speed	550 rpm on 0.5mm EXG
THK	Control at 1.15μm before Post-bake
Pre-bake	100°C*2.5min, directly
Power	80mJ/ cm² & 50μm @40mW
Dev.	60~70 sec in 1:99 SEDR-5/ 0.15MPa & 25 °C
Rinse	20sec/ 0.15MPa & 25 °C
HPMJ	10sec/ 0.4MPa & 25 °C
Post-bake	230 °C*30min clean oven

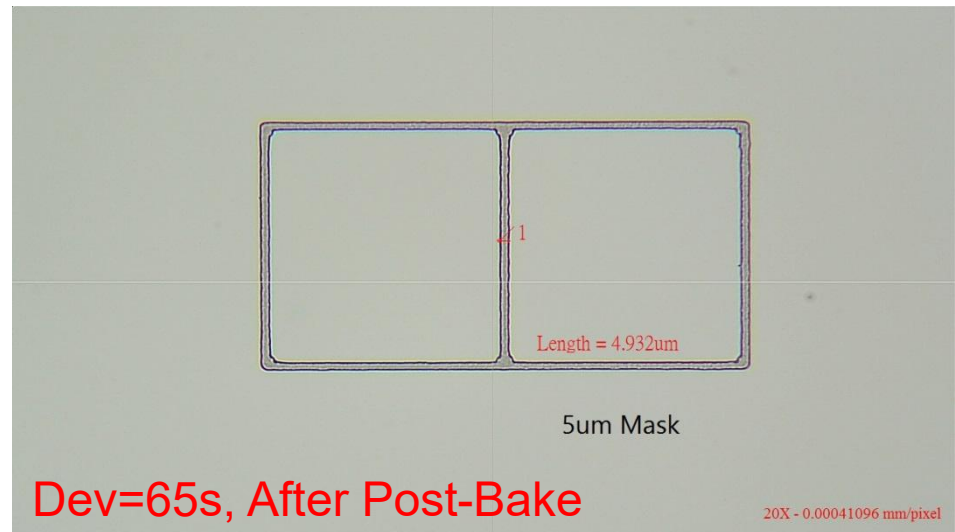
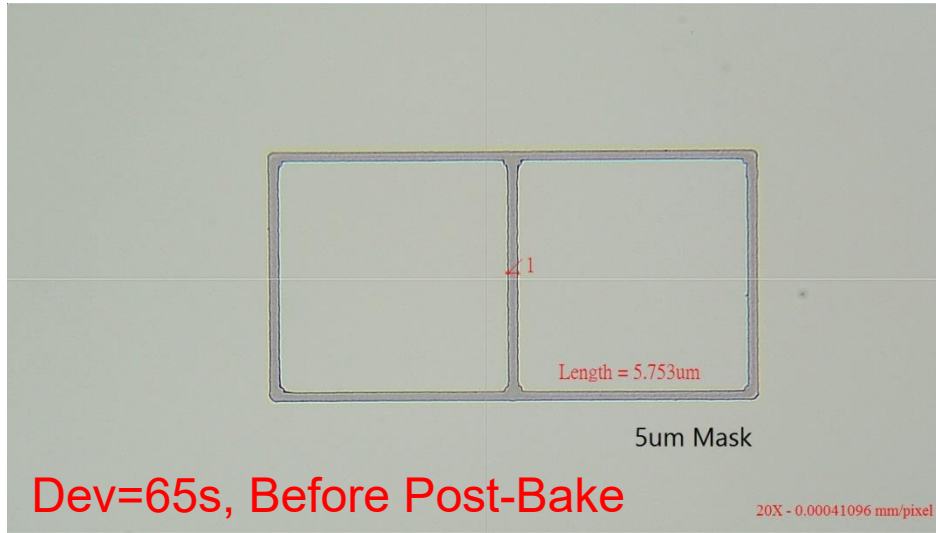
Profile ~ 10 μ m Pattern SEM



THK=1.06 μ m, Exp. Dose=80mJ/cm², Gap=50 μ m, Dev.=65s, Postbake=230°C *30min

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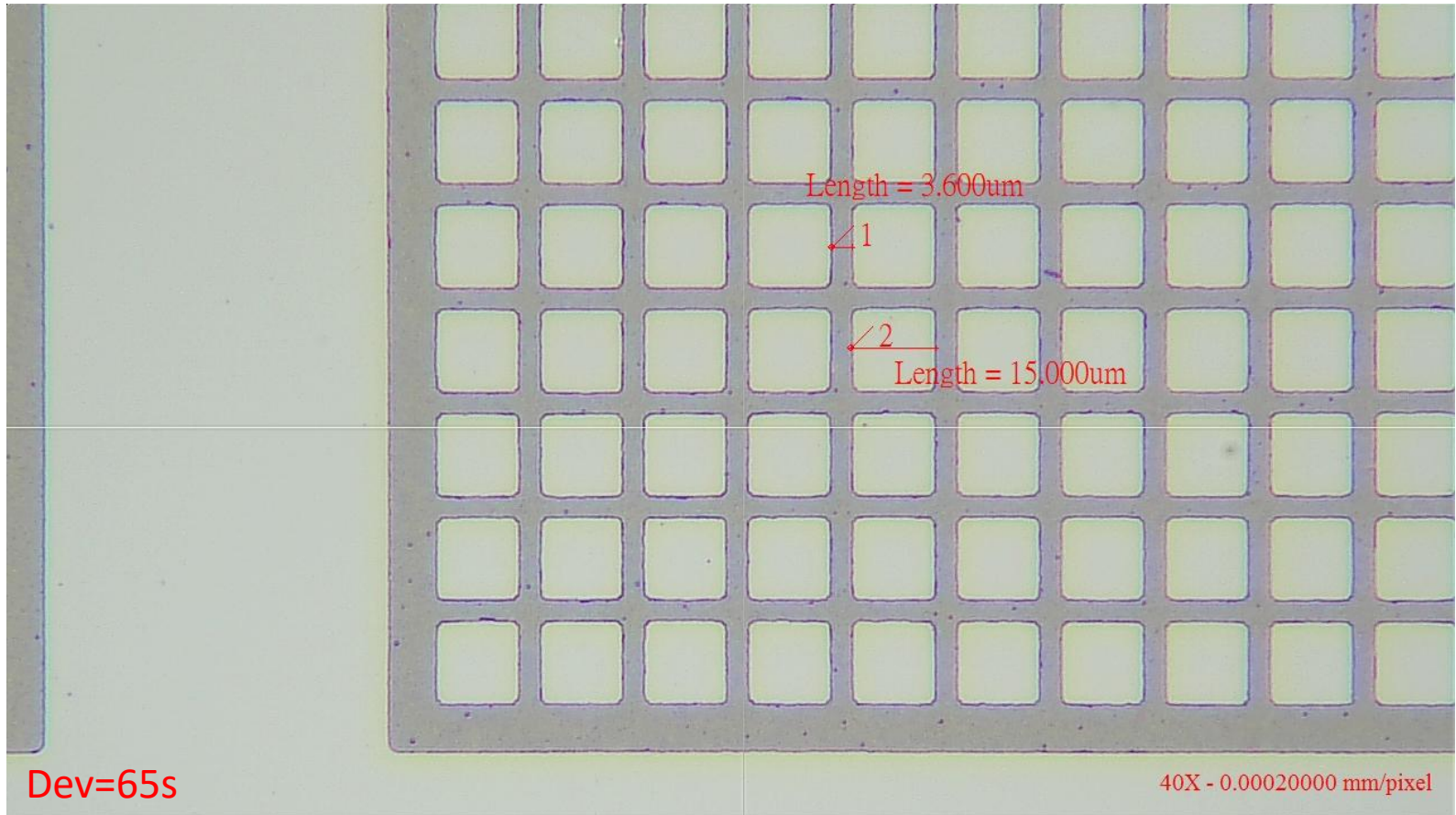
Profile ~ 5 μ m Pattern OM



THK=1.06 μ m, Exp. Dose=80mJ/cm², Gap=50 μ m, Postbake=230 $^{\circ}$ C *30min

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Profile ~ 3 μ m Pattern OM



THK=1.06 μ m, Exp. Dose=80mJ/cm², Gap=50 μ m, Postbake=230°C *30min

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